

Final datasheet
CoolSiC™ 1400 V SiC MOSFET G2 : Silicon Carbide MOSFET with .XT interconnection technology

特徴

- $V_{DS} = 1400\text{ V}$ at $T_{vj} = 25^{\circ}\text{C}$
- $I_{DC} = 65\text{ A}$ at $T_C = 100^{\circ}\text{C}$
- $R_{DS(on)} = 19\text{ m}\Omega$ at $V_{GS} = 18\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$
- Very low switching losses
- Short circuit withstand time $2\text{ }\mu\text{s}$
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.2\text{ V}$
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- 最適なインフィニオン製ゲートドライバーは以下でご覧になれます。
<https://www.infineon.com/gdfinder>

可能性のある用途

- General purpose drives (GPD)
- EV Charging
- Online UPS / Industrial UPS
- String inverter
- Energy storage systems (ESS)
- Welding

製品検証

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

詳細

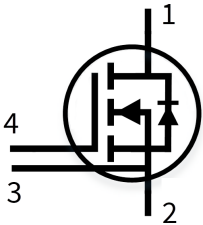
Pin definition:

- Pin 1 – Drain
- Pin 2 – Source
- Pin 3 – Kelvin sense contact
- Pin 4 – Gate

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction



- Halogen-free
- Green
- Lead-free
- RoHS



Type	Package	Marking
IMZC140R019M2H	PG-TO247-4-U07	14M2H019



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1 ハウジング

1 ハウジング

表 1 電気的特性

項目	記号	条件及び注記	規格値			単位
			最小	標準	最大	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	Wave soldering only allowed at leads 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{\text{th(j-a)}}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{\text{th(j-c)}}$			0.3	0.39	K/W

2 MOSFET

表 2 最大定格

項目	記号	条件及び注記		定格値	単位
ドレイン・ソース間電圧	V_{DSS}	$T_{\text{vj}} \geq 25\text{ °C}$		1400	V
Continuous DC drain current for $R_{\text{th(j-c,max)}}$, limited by $T_{\text{vj(max)}}$	I_{DDC}	$V_{\text{GS}} = 18\text{ V}$	$T_{\text{c}} = 25\text{ °C}$	92	A
			$T_{\text{c}} = 100\text{ °C}$	65	
Peak drain current, t_{p} limited by $T_{\text{vj(max)}}$ ¹⁾	I_{DM}	$V_{\text{GS}} = 18\text{ V}$		325	A
Gate-source voltage, max. transient voltage	V_{GS}	$t_{\text{p}} \leq 0.5\text{ }\mu\text{s}$, $D < 0.01$		-10...25	V
Gate-source voltage, max. static voltage ²⁾	V_{GS}			-7...23	V
Avalanche energy, single pulse	E_{AS}	$I_{\text{D}} = 40.4\text{ A}$, $V_{\text{DD}} = 50\text{ V}$, $L = 0.6\text{ mH}$, $T_{\text{vj(start)}} = 25\text{ °C}$		506	mJ
Avalanche energy, repetitive	E_{AR}	$I_{\text{D}} = 40.4\text{ A}$, $V_{\text{DD}} = 50\text{ V}$, $L = 3.1\text{ }\mu\text{H}$, $T_{\text{vj(start)}} = 25\text{ °C}$		2.5	mJ
Short-circuit withstand time	t_{SC}	$V_{\text{DD}} \leq 800\text{ V}$, $V_{\text{DS,peak}} < 1400\text{ V}$, $V_{\text{GS(on)}} = 15\text{ V}$, $T_{\text{vj(start)}} = 25\text{ °C}$		2	μs
Power dissipation, limited by $T_{\text{vj(max)}}$	P_{tot}	$T_{\text{c}} = 25\text{ °C}$		380	W
		$T_{\text{c}} = 100\text{ °C}$		190	

1) Verified by design.

2) The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

表 3 推奨値

項目	記号	条件及び注記	[JA]Values	単位
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

表 4 電気的特性

項目	記号	条件及び注記	規格値			単位
			最小	標準	最大	
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 40.4 \text{ A}$		$T_{vj} = 25^\circ\text{C}, V_{GS(on)} = 18 \text{ V}$		mΩ
				$T_{vj} = 150^\circ\text{C}, V_{GS(on)} = 18 \text{ V}$	41.1	
				$T_{vj} = 175^\circ\text{C}, V_{GS(on)} = 18 \text{ V}$	48	
				$T_{vj} = 25^\circ\text{C}, V_{GS(on)} = 15 \text{ V}$	23	
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 12.7 \text{ mA}, V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20 \text{ V}$)	3.5	$T_{vj} = 25^\circ\text{C}$	4.2	V
				$T_{vj} = 175^\circ\text{C}$	3.2	
Zero gate-voltage drain current	I_{DSS}	$V_{DS} = 1400 \text{ V}, V_{GS} = 0 \text{ V}$		$T_{vj} = 25^\circ\text{C}$	300	μA
				$T_{vj} = 175^\circ\text{C}$	5.1	
Gate leakage current	I_{GSS}	$V_{DS} = 0 \text{ V}$		$V_{GS} = 23 \text{ V}$	120	nA
				$V_{GS} = -10 \text{ V}$	-120	
Forward transconductance	g_{fs}	$I_D = 40.4 \text{ A}, V_{DS} = 20 \text{ V}$		26		S
Internal gate resistance	$R_{G,int}$	$f = 1 \text{ MHz}, V_{AC} = 25 \text{ mV}$		2.1		Ω
Input capacitance	C_{iss}	$V_{DS} = 1000 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}, V_{AC} = 25 \text{ mV}$		2860		pF
Output capacitance	C_{oss}	$V_{DS} = 1000 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}, V_{AC} = 25 \text{ mV}$		99		pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 1000 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}, V_{AC} = 25 \text{ mV}$		9		pF
C_{oss} stored energy	E_{oss}	Calculated based on $C_{oss} = f(V_{DD})$		63		μJ
Output charge	Q_{oss}	Calculated based on $C_{oss} = f(V_{DD})$		172		nC
Effective output capacitance, energy related	$C_{o(er)}$	$V_{DS} = 0...1000 \text{ V}, V_{GS} = 0 \text{ V},$ Calculated based on E_{oss}		197		pF
Effective output capacitance, time related	$C_{o(tr)}$	$I_D = \text{constant}, V_{DS} = 0...1000 \text{ V}, V_{GS} = 0 \text{ V},$ Calculated based on Q_{oss}		215		pF

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表 4 (続き) 電気的特性

項目	記号	条件及び注記	規格値			単位
			最小	標準	最大	
Total gate charge	Q_G	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		78		nC
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		22		nC
Gate-drain charge	Q_{GD}	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		20		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25^\circ \text{C}$	8.9		ns
			$T_{vj} = 175^\circ \text{C}$	7.7		
Rise time	t_r	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25^\circ \text{C}$	5.3		ns
			$T_{vj} = 175^\circ \text{C}$	4.9		
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25^\circ \text{C}$	21		ns
			$T_{vj} = 175^\circ \text{C}$	24		
Fall time	t_f	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25^\circ \text{C}$	8.7		ns
			$T_{vj} = 175^\circ \text{C}$	9.5		
Turn-on energy	E_{on}	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25^\circ \text{C}$	386		μJ
			$T_{vj} = 175^\circ \text{C}$	1163		
Turn-off energy	E_{off}	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25^\circ \text{C}$	178		μJ
			$T_{vj} = 175^\circ \text{C}$	205		
Total switching energy ¹⁾	E_{tot}	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25^\circ \text{C}$	643		μJ
			$T_{vj} = 175^\circ \text{C}$	1695		

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3 Body diode (MOSFET)

表 4 (続き) 電気的特性

項目	記号	条件及び注記	規格値			単位
			最小	標準	最大	
Turn-on energy at -5 V	E_{on}	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = -5/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = -5 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	386		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	1194		
Turn-off energy at -5 V	E_{off}	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = -5/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = -5 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	82		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	96		
Total switching energy at -5 V ¹⁾	E_{tot}	$V_{DD} = 1000 \text{ V}$, $I_D = 40.4 \text{ A}$, $V_{GS} = -5/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 12 \text{ nH}$, diode: body diode at $V_{GS} = -5 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	547		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	1627		
Virtual junction temperature	T_{vj}		-55		175	$^\circ\text{C}$

1) including E_{fr}

注: The chip technology was characterized up to 200 kV/ μs . The measured dV/dt was limited by measurement test setup and package.
Characteristics at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified.

3 Body diode (MOSFET)

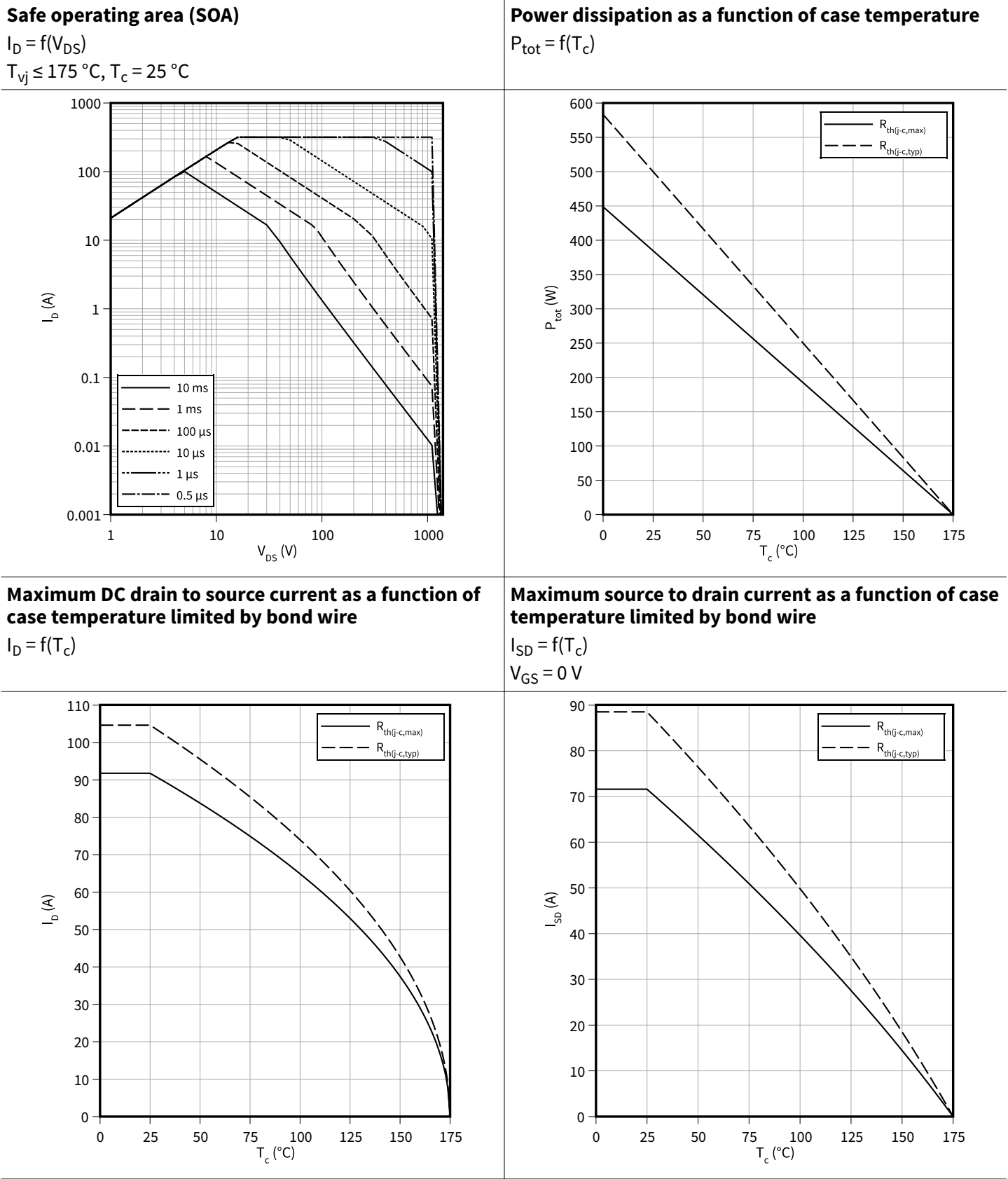
表 5 最大定格

項目	記号	条件及び注記	定格値	単位
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25 \text{ }^\circ\text{C}$	1400	V
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{SDC}	$V_{GS} = 0 \text{ V}$	$T_c = 25 \text{ }^\circ\text{C}$ $T_c = 100 \text{ }^\circ\text{C}$	A
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	$V_{GS} = 0 \text{ V}$	195	A

表 6 電気的特性

項目	記号	条件及び注記	規格値			単位
			最小	標準	最大	
Drain-source reverse voltage	V_{SD}	$I_{SD} = 40.4 \text{ A}$, $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	4.2	5.5	V
			$T_{vj} = 100 \text{ }^{\circ}\text{C}$	4.11		
			$T_{vj} = 175 \text{ }^{\circ}\text{C}$	4.05		
MOSFET forward recovery charge	Q_{fr}	$V_{DD} = 1000 \text{ V}$, $I_{SD} = 40.4 \text{ A}$, $V_{GS} = 0 \text{ V}$, $R_{GS(on)} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	0.46		μC
			$T_{vj} = 175 \text{ }^{\circ}\text{C}$	1.41		
MOSFET peak forward recovery current	I_{frm}	$V_{DD} = 1000 \text{ V}$, $I_{SD} = 40.4 \text{ A}$, $V_{GS} = 0 \text{ V}$, $R_{GS(on)} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	71		A
			$T_{vj} = 175 \text{ }^{\circ}\text{C}$	135		
MOSFET forward recovery energy	E_{fr}	$V_{DD} = 1000 \text{ V}$, $I_{SD} = 40.4 \text{ A}$, $V_{GS} = 0 \text{ V}$, $R_{GS(on)} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	79		μJ
			$T_{vj} = 175 \text{ }^{\circ}\text{C}$	327		
MOSFET forward recovery energy at -5 V	E_{fr}	$V_{DD} = 1000 \text{ V}$, $I_{SD} = 40.4 \text{ A}$, $V_{GS} = -5 \text{ V}$, $R_{GS(on)} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	79		μJ
			$T_{vj} = 175 \text{ }^{\circ}\text{C}$	337		
Virtual junction temperature	T_{vj}		-55		175	$^{\circ}\text{C}$

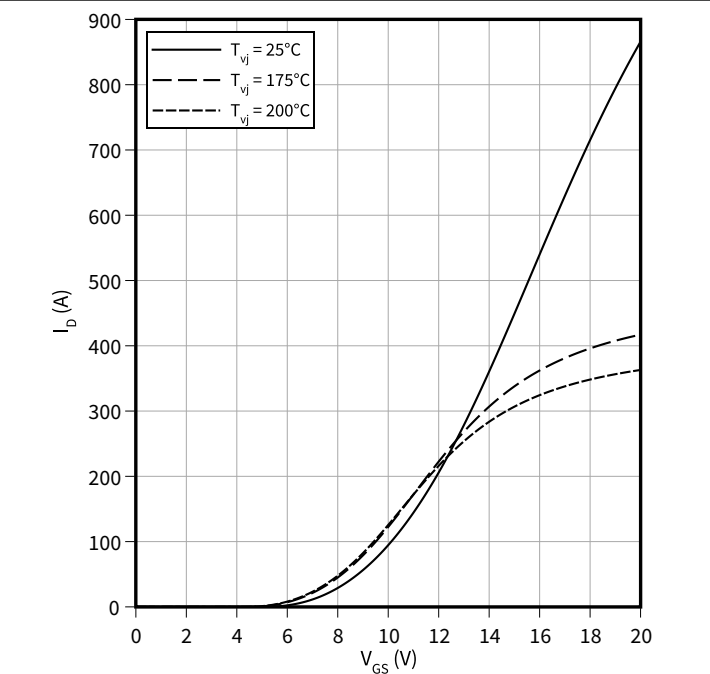
4 特性図



4 特性図

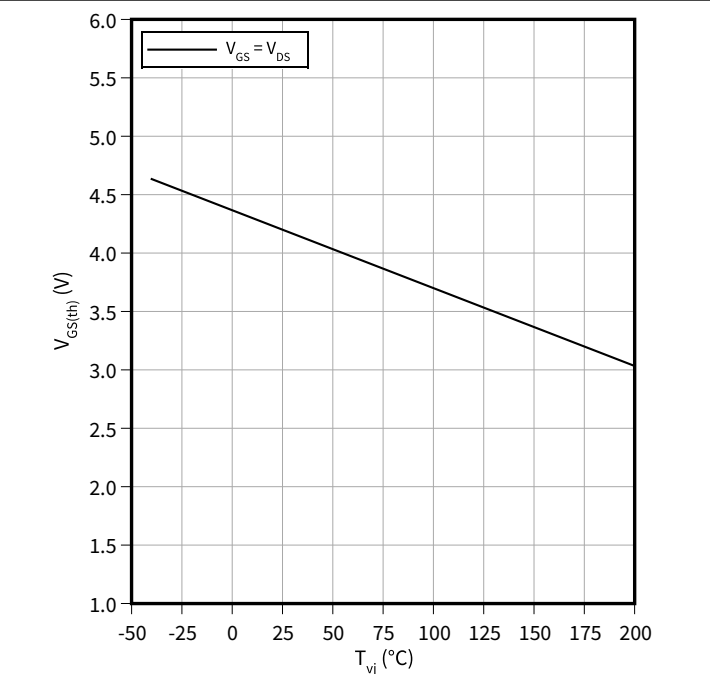
Typical transfer characteristic

$I_D = f(V_{GS})$
 $V_{DS} = 20\text{ V}$, $t_p = 20\text{ }\mu\text{s}$



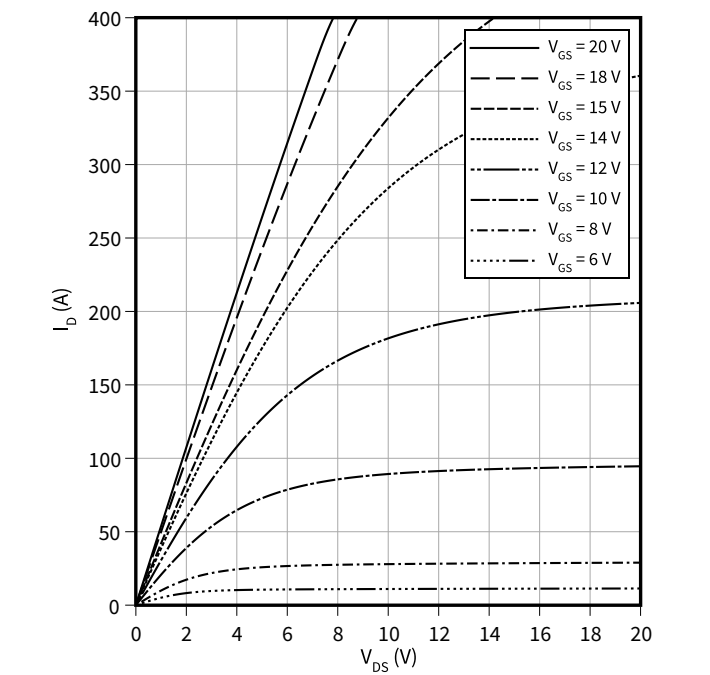
Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$
 $I_D = 12.7\text{ mA}$



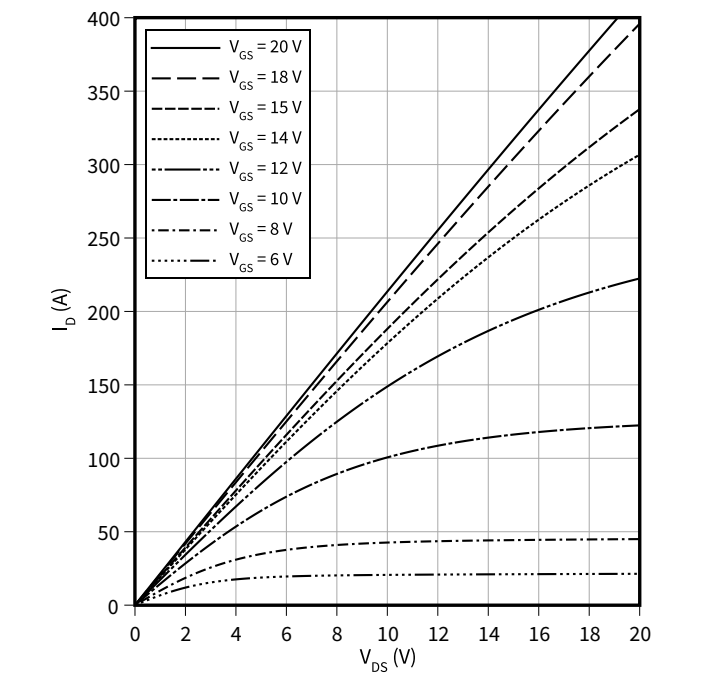
Typical output characteristic, V_{GS} as a parameter

$I_D = f(V_{DS})$
 $T_{vj} = 25\text{ }^\circ\text{C}$, $t_p = 20\text{ }\mu\text{s}$



Typical output characteristic, V_{GS} as a parameter

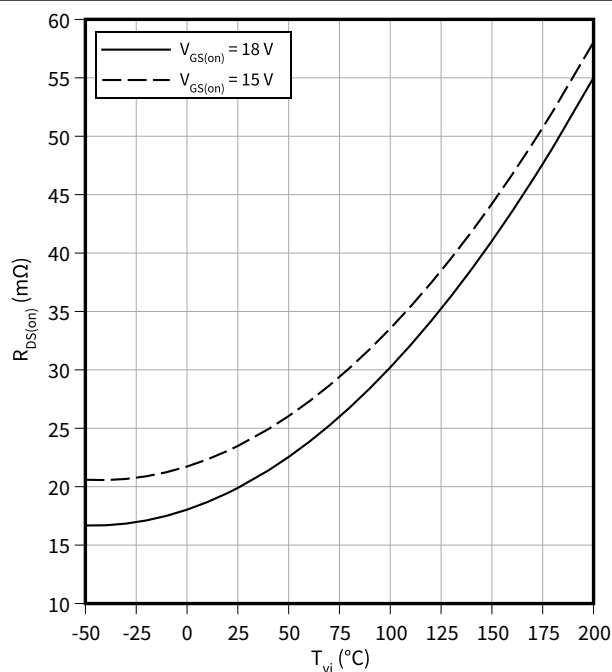
$I_D = f(V_{DS})$
 $T_{vj} = 175\text{ }^\circ\text{C}$, $t_p = 20\text{ }\mu\text{s}$



4 特性図

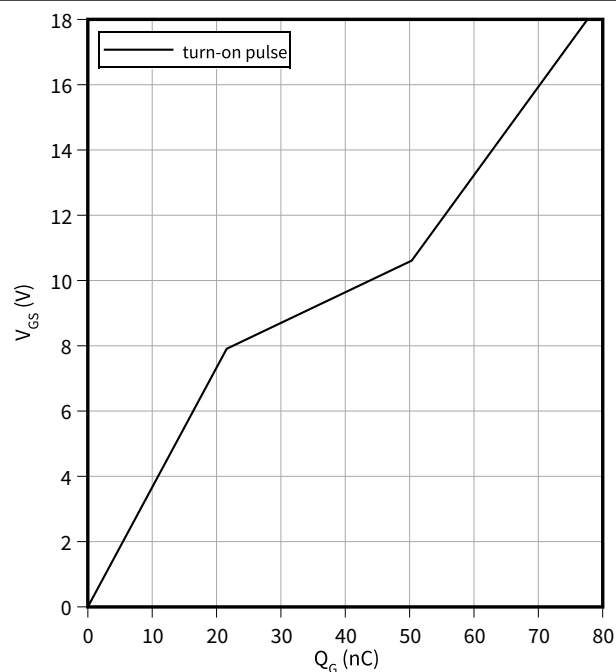
Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$
 $I_D = 40.4 \text{ A}$



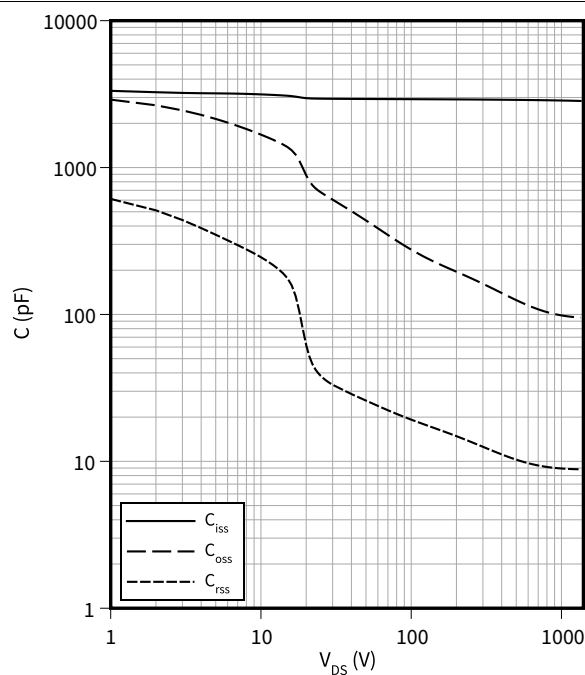
Typical gate charge

$V_{GS} = f(Q_G)$
 $I_D = 40.4 \text{ A}, V_{DS} = 1000 \text{ V}$



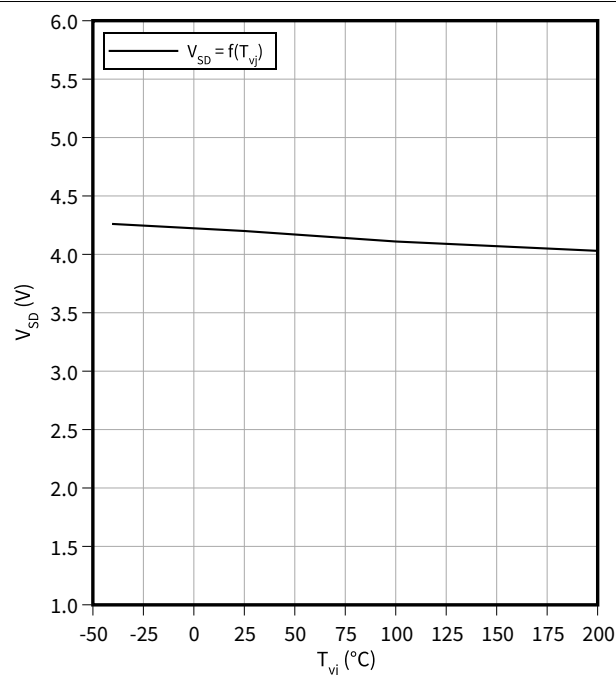
Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$
 $f = 100 \text{ kHz}, V_{GS} = 0 \text{ V}$



Typical reverse drain voltage as a function of junction temperature

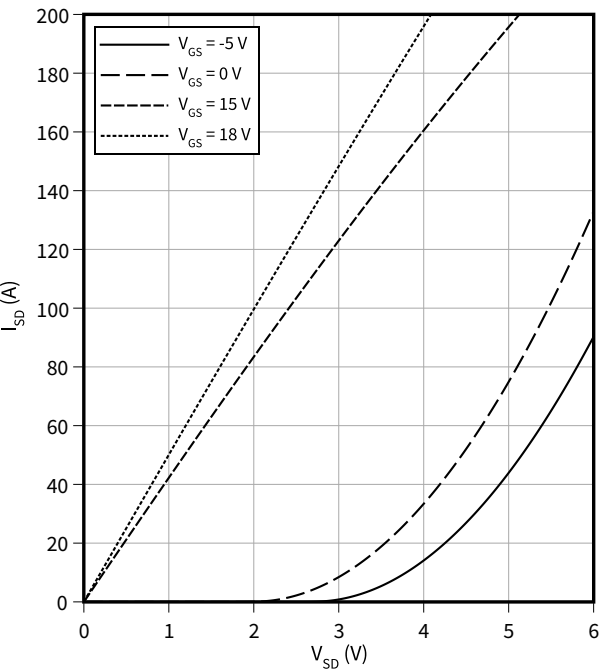
$V_{SD} = f(T_{vj})$
 $I_{SD} = 40.4 \text{ A}, V_{GS} = 0 \text{ V}$



4 特性図

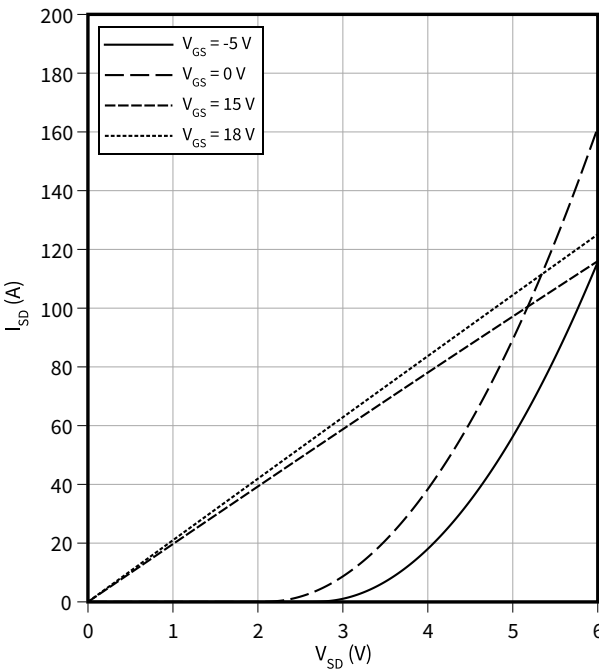
Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 25\text{ }^{\circ}\text{C}$, $t_p = 20\text{ }\mu\text{s}$



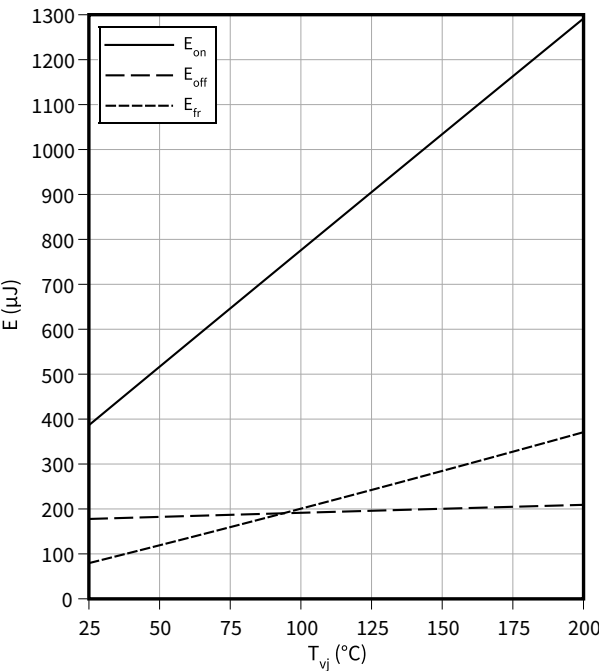
Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 175\text{ }^{\circ}\text{C}$, $t_p = 20\text{ }\mu\text{s}$



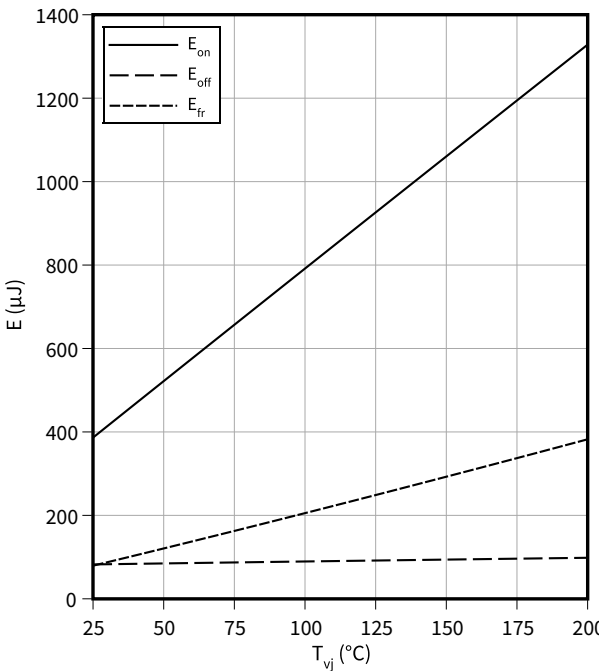
Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(T_{vj})$
 $V_{GS} = 0/18\text{ V}$, $I_D = 40.4\text{ A}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 1000\text{ V}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$E = f(T_{vj})$
 $V_{GS} = -5/18\text{ V}$, $I_D = 40.4\text{ A}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 1000\text{ V}$

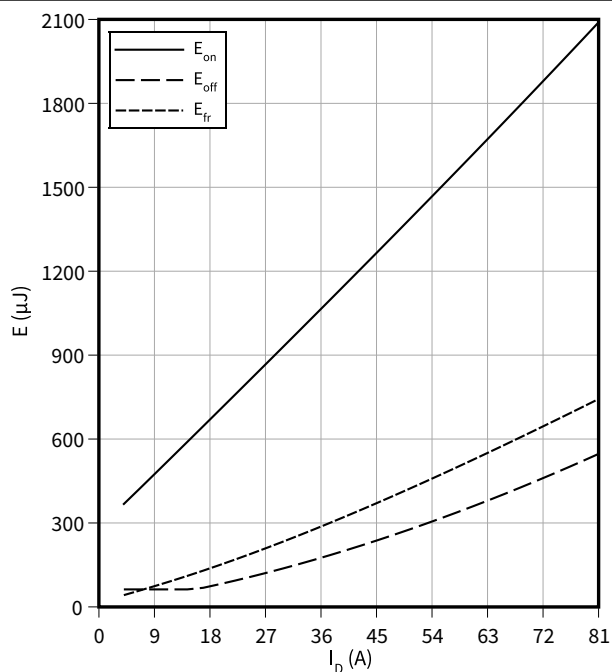


4 特性図

Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(I_D)$$

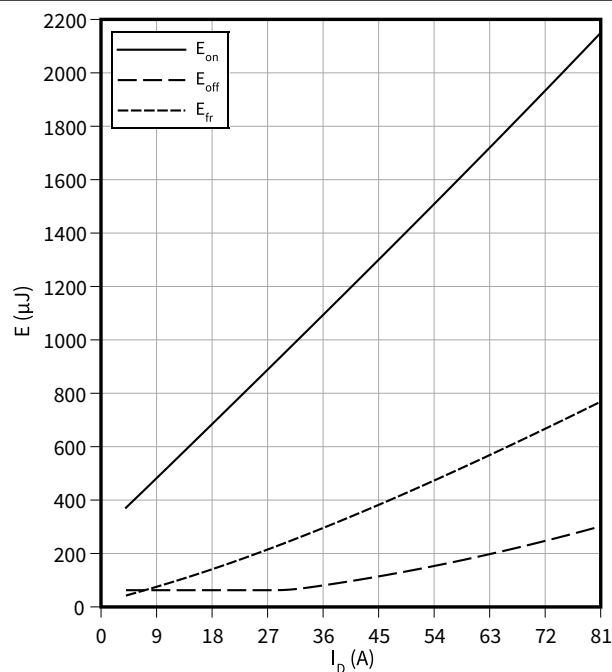
$V_{GS} = 0/18$ V, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω , $V_{DD} = 1000$ V



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5$ V

$$E = f(I_D)$$

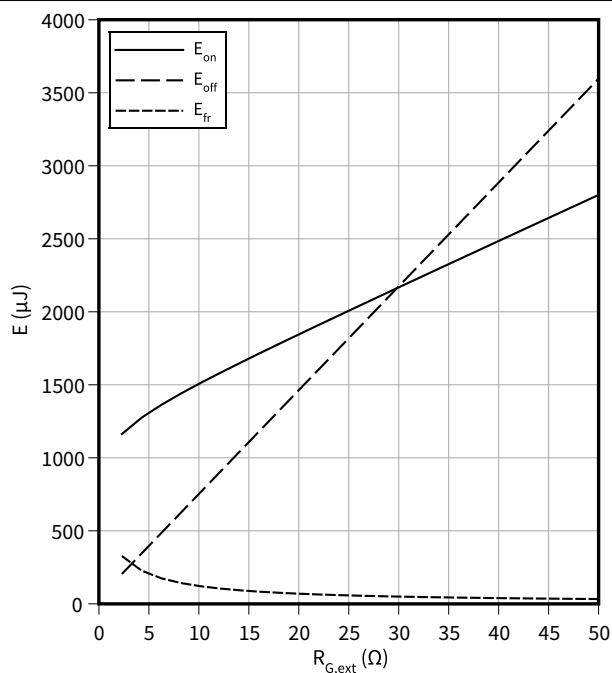
$V_{GS} = -5/18$ V, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω , $V_{DD} = 1000$ V



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(R_{G,ext})$$

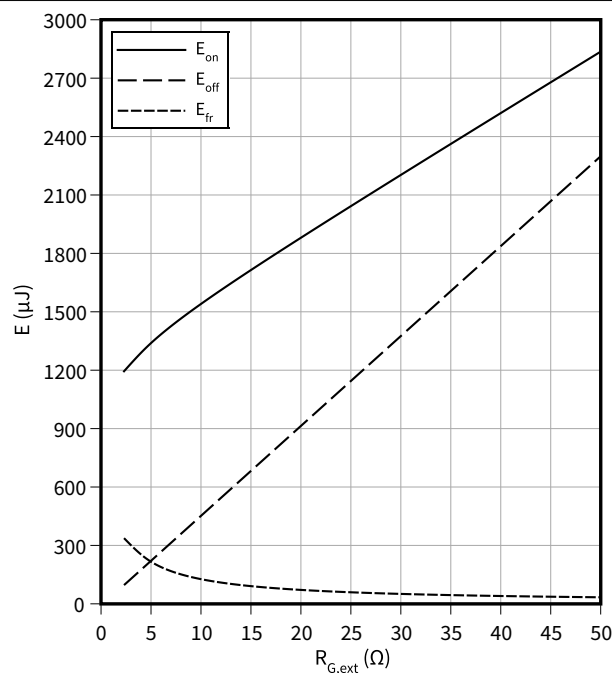
$V_{GS} = 0/18$ V, $I_D = 40.4$ A, $T_{vj} = 175$ °C, $V_{DD} = 1000$ V



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5$ V

$$E = f(R_{G,ext})$$

$V_{GS} = -5/18$ V, $I_D = 40.4$ A, $T_{vj} = 175$ °C, $V_{DD} = 1000$ V

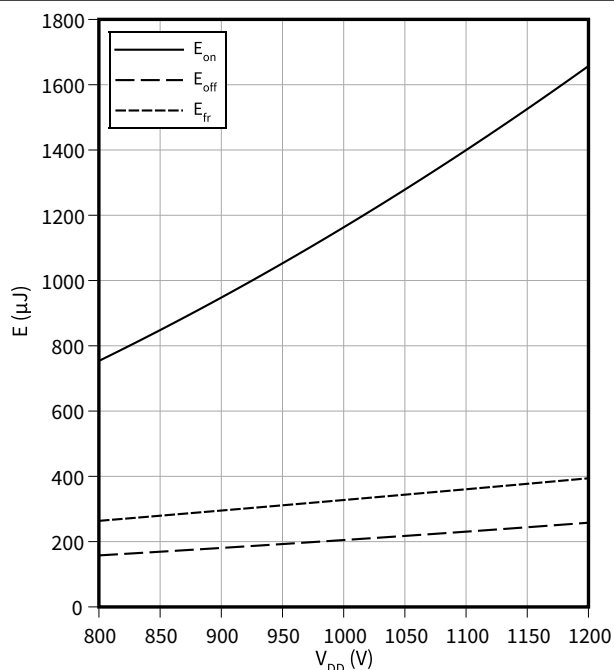


4 特性図

Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(V_{DD})$$

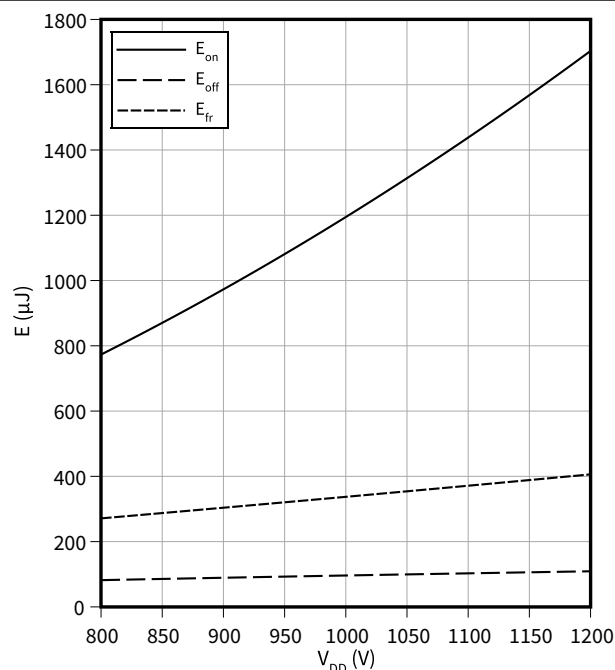
$V_{GS} = 0/18$ V, $I_D = 40.4$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω



Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5$ V

$$E = f(V_{DD})$$

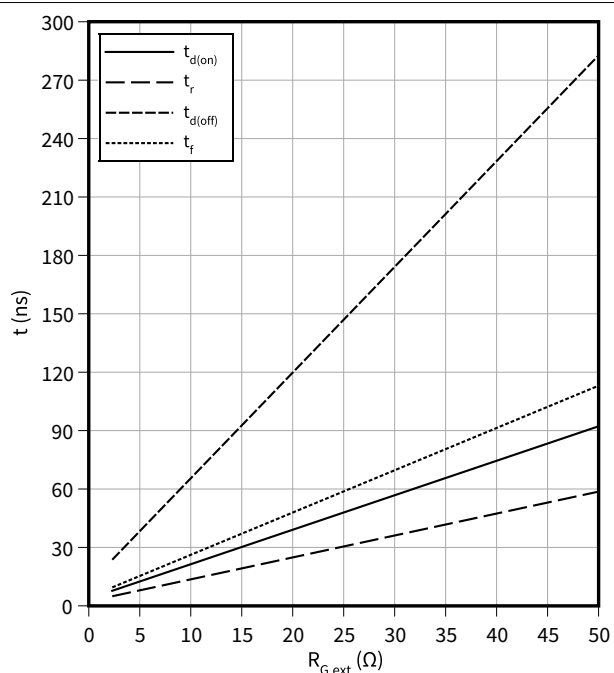
$V_{GS} = -5/18$ V, $I_D = 40.4$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$t = f(R_{G,ext})$$

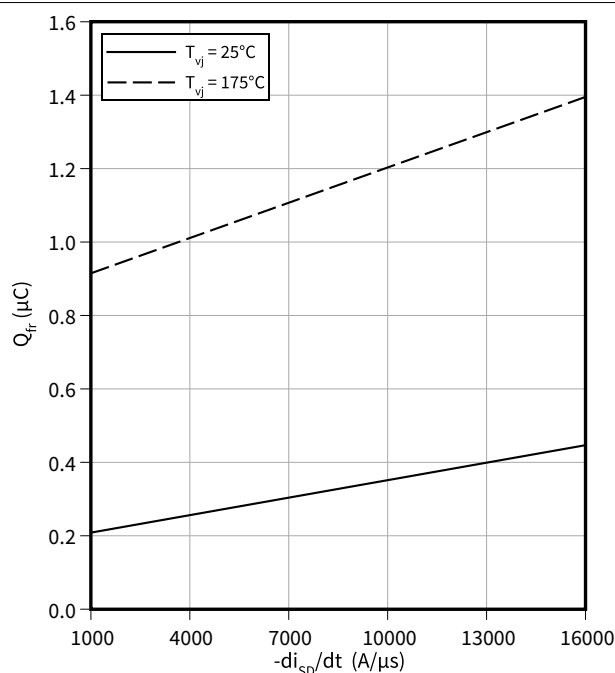
$V_{GS} = 0/18$ V, $I_D = 40.4$ A, $T_{vj} = 175$ °C, $V_{DD} = 1000$ V



Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$Q_{fr} = f(-di_{SD}/dt)$$

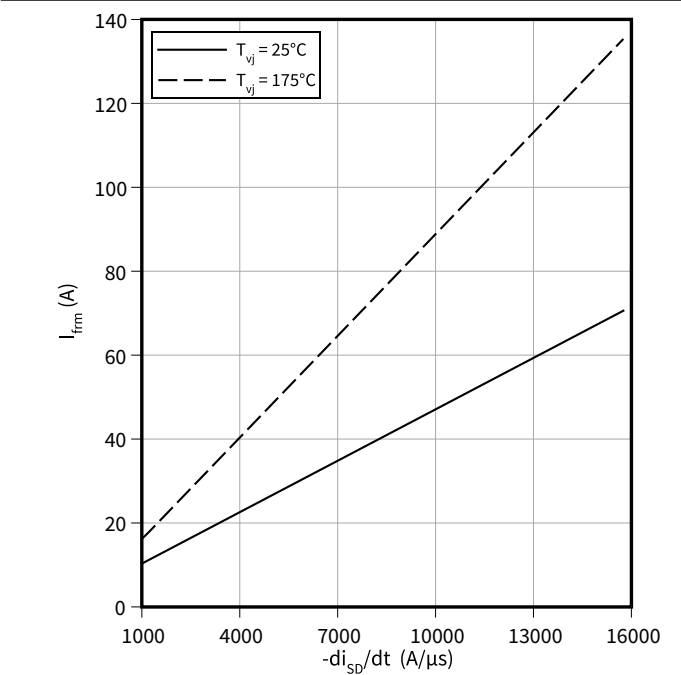
$V_{GS} = 0/18$ V, $I_{SD} = 40.4$ A, $V_{DD} = 1000$ V



4 特性図

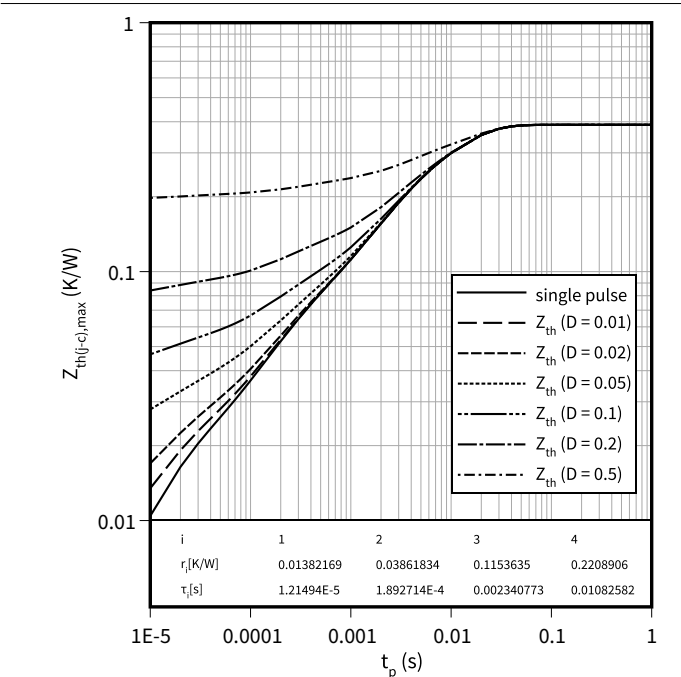
Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$I_{frm} = f(-di_{SD}/dt)$
 $V_{GS} = 0/18\text{ V}, I_{SD} = 40.4\text{ A}, V_{DD} = 1000\text{ V}$

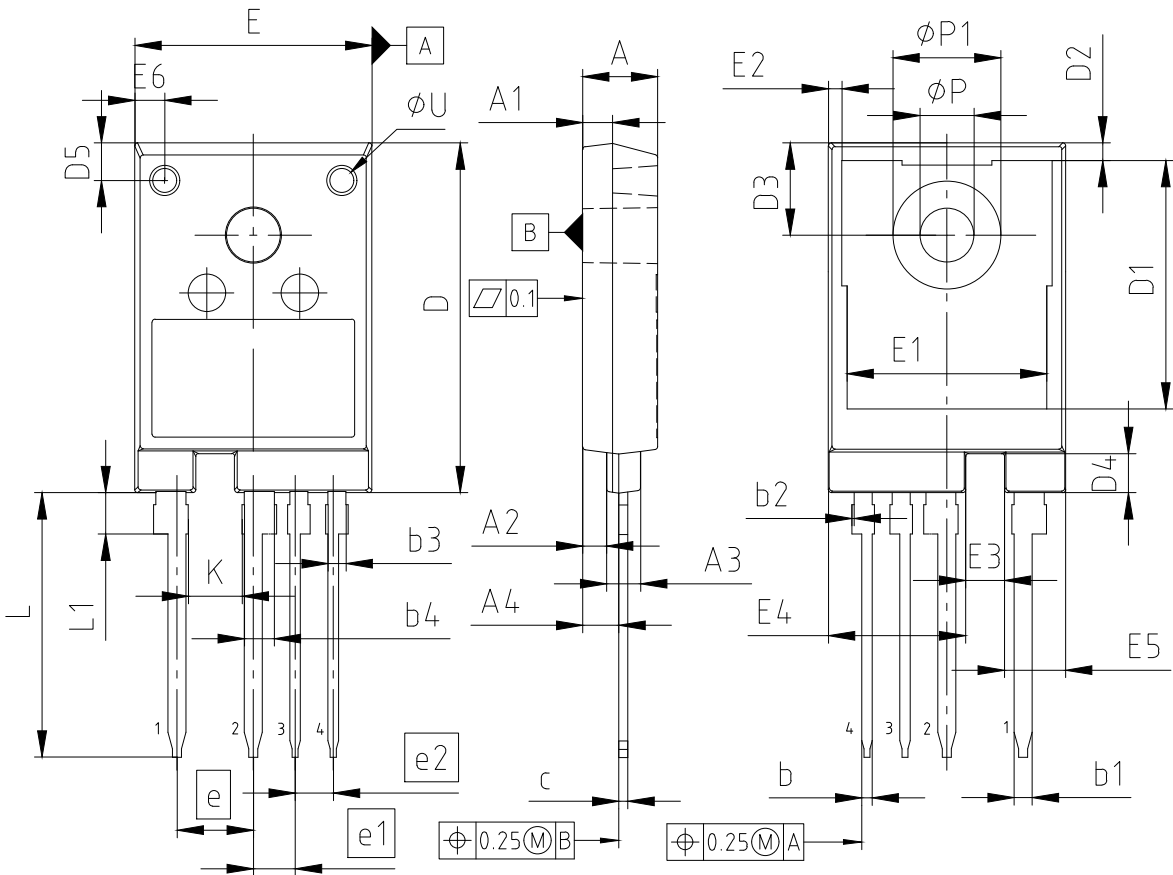


Max. transient thermal impedance (MOSFET/diode)

$Z_{th(j-c),max} = f(t_p)$
 $D = t_p/T$



5 パッケージ外形図



PACKAGE - GROUP NUMBER: PG-T0247-4-U07					
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	E	15.60	16.00
A1	1.90	2.10	E1	13.10	13.50
A2	1.50	1.70	E2	0.60	1.20
A3	2.16	2.36	E3	2.48	2.68
A4	2.31	2.51	E4	9.05	9.25
b	0.60	0.80	E5	3.97	4.17
b1	1.10	1.30	E6	1.80	2.20
b2	---	0.15	e	5.08	
b3	1.10	1.30	e1	2.79	
b4	1.90	2.10	e2	2.54	
c	0.50	0.70	K	3.50	---
D	23.10	23.50	L	17.50	17.80
D1	16.25	16.85	L1	2.61	2.91
D2	0.97	1.37	N	4	
D3	6.00	6.30	ØP1	7.00	7.40
D4	2.50	2.70	ØP	3.50	3.70
D5	2.30	2.70	ØU	1.40	1.80

NOTES: DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS
N IS THE NUMBER OF LEADS

図 1

6 Testing conditions

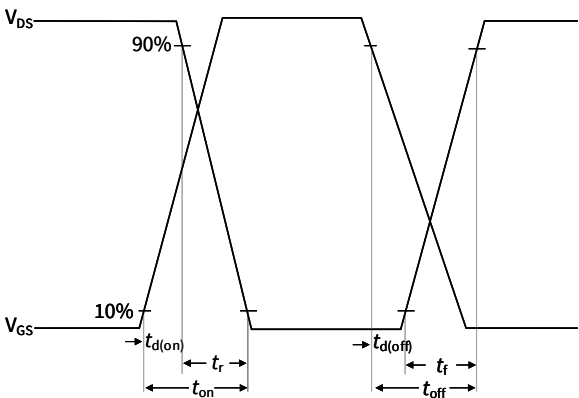


Figure A. Definition of switching times

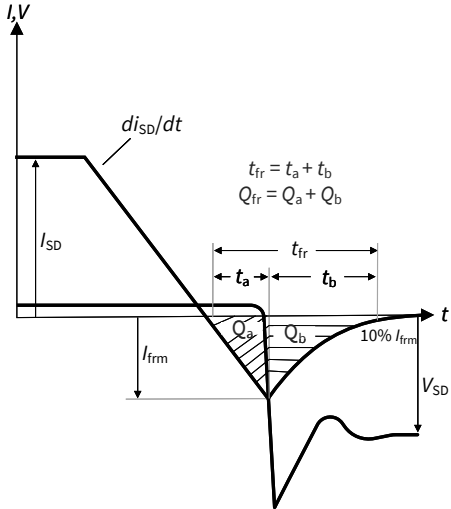


Figure B. Definition of body diode switching characteristics

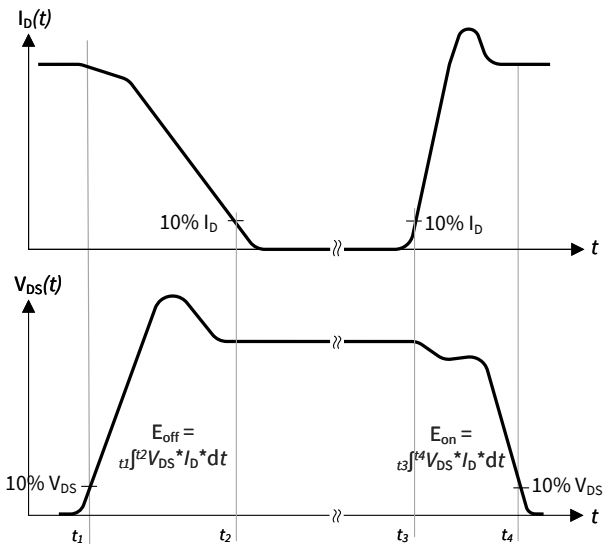


Figure C. Definition of switching losses

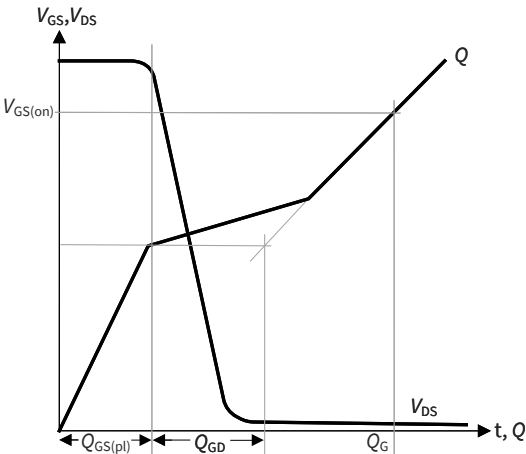


Figure D. Definition of QGD

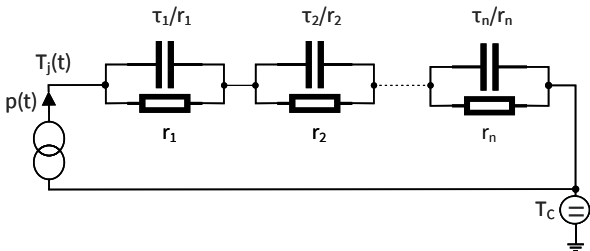


Figure E. Thermal equivalent circuit

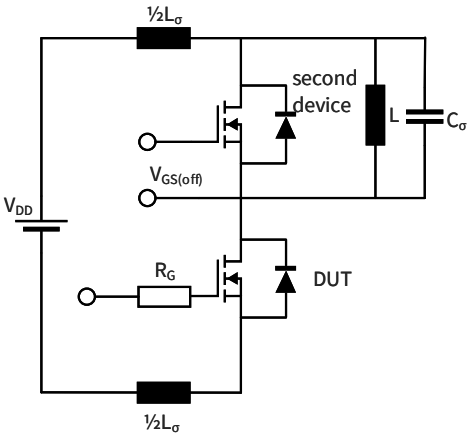


Figure F. Dynamic test circuit
Parasitic inductance L_{σ} ,
Parasitic capacitor C_{σ} ,



改訂履歴

改訂履歴

文書改訂	発行日	変更内容
0.10	2025-05-28	Preliminary datasheet
1.00	2025-06-12	Final datasheet

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